

勝特力材料 886-3-5753170
 胜特力电子(上海) 86-21-54151736
 胜特力电子(深圳) 86-755-83298787

[Http://www.100y.com.tw](http://www.100y.com.tw)

TOSHIBA

2SK1120

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π -MOSII⁵)

2SK1120

DC-DC Converter and Motor Drive Applications

- Low drain-source ON resistance : $R_{DS(ON)} = 1.5 \Omega$ (typ.)
- High forward transfer admittance : $|Y_{fs}| = 4.0 \text{ S}$ (typ.)
- Low leakage current : $I_{DSS} = 300 \mu\text{A}$ (max) ($V_{DS} = 800 \text{ V}$)
- Enhancement-mode : $V_{th} = 1.5 \sim 3.5 \text{ V}$ ($V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$)

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	1000	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	1000	V
Gate-source voltage		V_{GSS}	± 20	V
Drain current	DC (Note 1)	I_D	8	A
	Pulse (Note 1)	I_{DP}	24	
Drain power dissipation ($T_c = 25^\circ\text{C}$)		P_D	150	W
Channel temperature		T_{ch}	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	-55~150	$^\circ\text{C}$

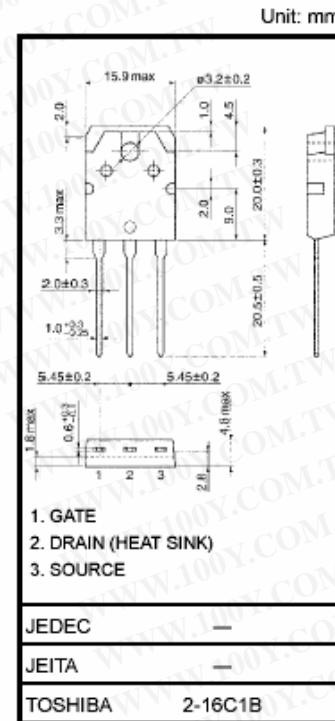
Thermal Characteristics

Characteristics		Symbol	Max	Unit
Thermal resistance, channel to case		$R_{th}(ch-c)$	0.833	$^\circ\text{C}/\text{W}$
Thermal resistance, channel to ambient		$R_{th}(ch-a)$	50	$^\circ\text{C}/\text{W}$

Note 1: Please use devices on condition that the channel temperature is below 150°C.

This transistor is an electrostatic sensitive device.

Please handle with caution.



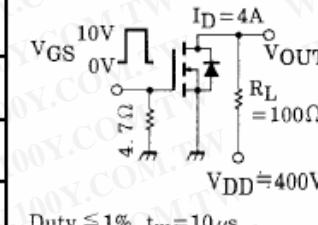
Weight: 4.6 g (typ.)

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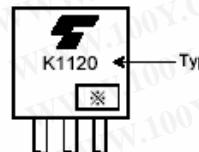
Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	I_{GSS}	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$	—	—	± 100	nA
Drain cut-off current	I_{DSS}	$V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$	—	—	300	μA
Drain-source breakdown voltage	$V_{(BR) DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	1000	—	—	V
Gate threshold voltage	V_{th}	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	1.5	—	3.5	V
Drain-source ON resistance	$R_{DS (\text{ON})}$	$V_{GS} = 10\text{ V}, I_D = 4\text{ A}$	—	1.5	1.8	Ω
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 20\text{ V}, I_D = 4\text{ A}$	2.0	4.0	—	S
Input capacitance	C_{iss}	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	1300	—	pF
Reverse transfer capacitance	C_{rss}		—	100	—	
Output capacitance	C_{oss}		—	180	—	
Switching time	Rise time	t_r		—	25	—
	Turn-on time	t_{on}		—	40	—
	Fall time	t_f		—	20	—
	Turn-off time	t_{off}		—	100	—
Total gate charge (Gate-source plus gate-drain)	Q_g	$V_{DD} = 400\text{ V}, V_{GS} = 10\text{ V}, I_D = 8\text{ A}$	—	120	—	nC
Gate-source charge	Q_{gs}		—	70	—	
Gate-drain ("Miller") charge	Q_{gd}		—	50	—	

Source-Drain Ratings and Characteristics ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	8	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	24	A
Forward voltage (diode)	V_{DSF}	$I_{DR} = 8\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.9	V

Marking



※ Lot Number

□ □ Month (starting from alphabet A)

□ Year (last number of the christian era)